



Improved Quad SPST CMOS Analog Switches

DESCRIPTION

The DG441B, DG442B are monolithic quad analog switches designed to provide high speed, low error switching of analog and audio signals. The DG441B, DG442B are upgrades to the original DG441, DG442.

Combing low on-resistance (45 Ω , typ.) with high speed (t_{ON} 120 ns, typ.), the DG441B, DG442B are ideally suited for Data Acquisition, Communication Systems, Automatic Test Equipment, or Medical Instrumentation. Charge injection has been minimized on the drain for use in sample-and-hold circuits.

The DG441B, DG442B are built using Vishay Siliconix's high-voltage silicon-gate process. An epitaxial layer prevents latchup.

When on, each switch conducts equally well in both directions and blocks input voltages to the supply levels when off.

FEATURES

- Low On-Resistance: 45 Ω
- Low Power Consumption: 1 mW
- Fast Switching Action t_{ON}: 120 ns
- Low Charge Injection Q: 1 pC
- TTL/CMOS-Compatible Logic
- Single Supply Capability
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

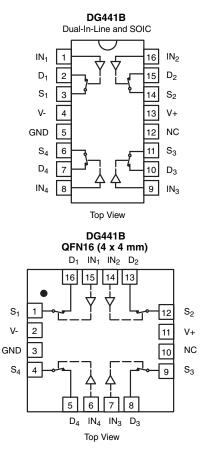
BENEFITS

- Less Signal Errors and Distortion
- Reduced Power Supply Requirements
- Faster Throughput
- Reduced Pedestal Errors
- Simple Interfacing

APPLICATIONS

- Audio Switching
- Data Acquisition
- Sample-and-Hold Circuits
- Communication Systems
- Automatic Test Equipment
- Medical Instruments

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLELogicDG441BDG442B0ONOFF1OFFON

 $\begin{array}{l} \text{Logic "0"} \leq 0.8 \ \text{V} \\ \text{Logic "1"} \geq 2.4 \ \text{V} \end{array}$

ORDERING INFORMATION					
Temp Range	Package	Part Number			
		DG441BDJ			
	16-pin Plastic DIP	DG441BDJ-E3			
- 40 °C to 85 °C		DG442BDJ			
		DG442BDJ-E3			
	16-pin Narrow SOIC	DG441BDY-E3			
		DG441BDY-T1-E3			
		DG442BDY-E3			
		DG442BDY-T1-E3			
	16 pin QFN 4 x 4 mm	DG441BDN-T1-E4			
	(Variation 1)	DG442BDN-T1-E4			

 Document Number: 72625
 For technical questions, contact: pmostechsupport@vishay.com
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COMPLIANT

HALOGEN

FRFF

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ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)							
Parameter		Symbol	Limit	Unit			
V+ to V-			44				
GND to V-			25	v			
Digital Inputs ^a , V _S , V _D			(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first				
Continuous Current (Any Termina	al)		30				
Current, S or D (Pulsed at 1 ms,	10 % duty cycle)		100	- mA			
Storage Temperature			- 65 to 125	°C			
Power Dissipation (Package) ^b	16-pin Plastic DIP ^c		470				
	16-pin Narrow Body SOIC ^d		900	mW			
	QFN-16 ^d		850	1			

Notes:

a. Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC Board.

c. Derate 6 mW/°C above 75 °C.

d. Derate 12 mW/°C above 75 °C.



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· ·		Test Conditions			Limits		
		Unless Otherwise Specified V+ = 15 V, V- = -15 V		- 4	0 °C to 85	°C	
Parameter	Symbol	$V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^e$	Temp. ^b	Min. ^d	Typ. ^c	Max. ^d	Unit
Analog Switch					•	•	
Analog Signal Range ^e	V _{ANALOG}		Full	- 15		15	V
Drain-Source On-Resistance	R _{DS(on)}	$I_{\rm S} = 1$ mA, $V_{\rm D} = \pm 10$ V	Room Full		45	80 95	Ω
On-Resistance Match Between Channels ^e	$\Delta R_{DS(on)}$	$I_{S} = 1 \text{ mA}, V_{D} = \pm 10 \text{ V}$	Room Full		2	4 5	52
Switch Off Leakage Current	I _{S(off)}	$V_{D} = \pm 14 \text{ V}, \text{ V}_{S} = \pm 14 \text{ V}$	Room Full	- 0.5 - 5	± 0.01	0.5 5	nA
	I _{D(off)}		Room Full	- 0.5 - 5	± 0.01	0.5 5	
Channel On Leakage Current	I _{D(on)}	$V_{S} = V_{D} = \pm 14 V$	Room Full	- 0.5 - 10	± 0.02	0.5 10	
Digital Control							
Input Voltage Low	V _{INL}		Full			0.8	v
Input Voltage High	V _{INH}		Full	2.4			v
Input Current V _{IN} Low	I _{INL}	V _{IN} under test = 0.8 V All Other = 2.4 V	Full	- 1	- 0.01	1	μA
Input Current V _{IN} High	I _{INH}	V _{IN} under test = 2.4 V All Other = 0.8 V	Full	- 1	0.01	1	μΑ
Dynamic Characteristics					•	•	
Turn-On Time	t _{ON}	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$	Room		120	220	ns
Turn-Off Time	t _{OFF}	$V_{S} = 10$ V, See Figure 2	Room		65	120	115
Charge Injection ^e	Q	$C_L = 1 \text{ nF}, V_S = 0 \text{ V}$ $V_{gen} = 0 \text{ V}, R_{gen} = 0 \Omega$	Room		- 1		pC
Off Isolation ^e	OIRR	$R_L = 50 \Omega$, $C_L = 15 pF$	Room		- 90		dB
Crosstalk (Channel-to-Channel)	X _{TALK}	$V_{S} = 1 V_{RMS}$, f = 100 kHz	Room		- 95		UD
SourceOff Capacitance ^e	C _{S(off)}	f = 1 MHz	Room		4		
Drain Off Capacitance ^e	C _{D(off)}		Room		4		pF
Channel On Capacitance ^e	C _{D(on)}	$V_{S} = V_{D} = 0 V, f = 1 MHz$	Room		16		
Power Supplies			Room		1	1	
Positive Supply Current	l+	V+ = 16.5 V, V- = - 16.5 V	Full			5	μA
Negative Supply Current	I-	$V_{IN} = 0 \text{ or } 5 \text{ V}$	Room Full	- 1 - 5			Pro 1

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SPECIFICATIONS (for single supply)							
		Test Conditions Unless Otherwise Specified		Limits - 40 °C to 85 °C			
Parameter	Symbol	V+ = 12 V, V- = 0 V V _{IN} = 2.4 V, 0.8 V ^e	Temp. ^b	Min. ^d	Typ. ^c	Max. ^d	Unit
Analog Switch							
Analog Signal Range ^e	V _{ANALOG}		Full	0		12	V
Drain-Source On-Resistance	R _{DS(on)}	$I_{\rm S}$ = 1 mA, $V_{\rm D}$ = 3 V, 8 V	Room Full		90	160 200	Ω
Dynamic Characteristics						•	
Turn-On Time	t _{ON}	R _L = 1 kΩ, C _L = 35 pF, V _S = 8 V	Room		120	300	-
Turn-Off Time	t _{OFF}	See Figure 2	Room		60	200	ns
Charge Injection	Q	$C_L = 1 \text{ nF}, V_{gen} = 6 \text{ V}, R_{gen} = 0 \Omega$	Room		4		рС
Power Supplies							
Positive Supply Current	l+	V _{IN} = 0 V or 5 V	Room Full			1 5	
Negative Supply Current	-	VIN - 5 V 01 5 V	Room Full	- 1 - 5			μA

Notes:

a. Refer to PROCESS OPTION FLOWCHART.

b. Room = 25 °C, Full = as determined by the operating temperature suffix.

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

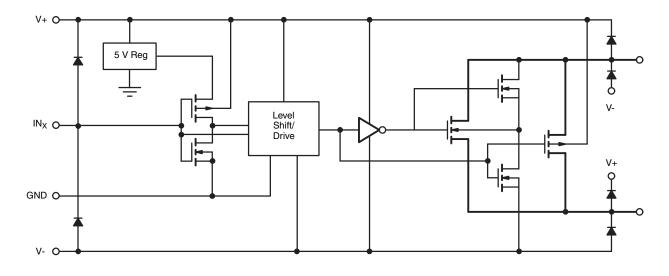
d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

e. Guaranteed by design, not subject to production test.

f. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

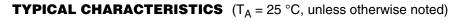
SCHEMATIC DIAGRAM (typical channel)

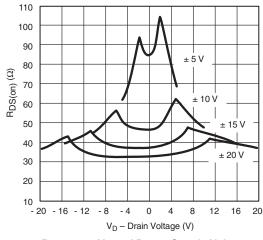




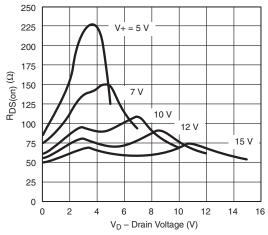


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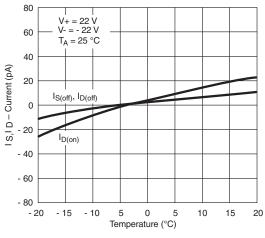




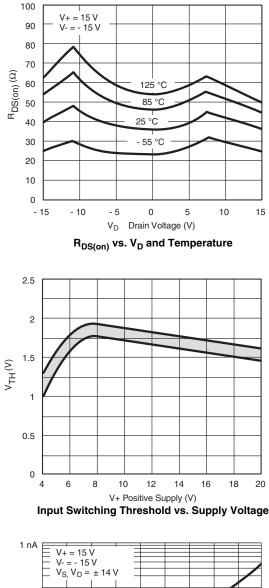
R_{DS(on)} vs. V_D and Power Supply Voltages

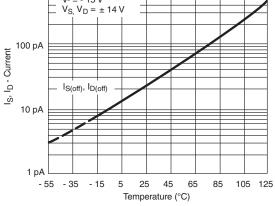


R_{DS(on)} vs. V_D and Single Power Supply Voltages



Leakage Currents vs. Analog Voltage



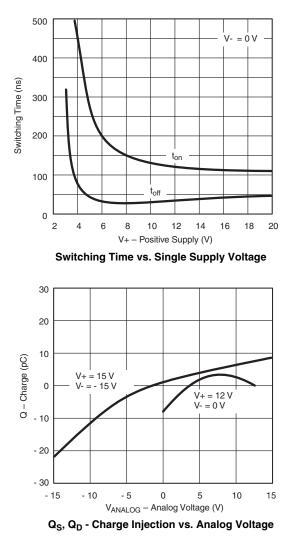


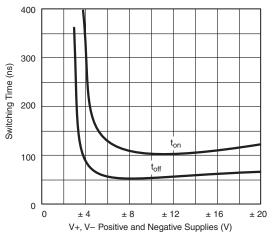
Leakage Currents vs. Temperature

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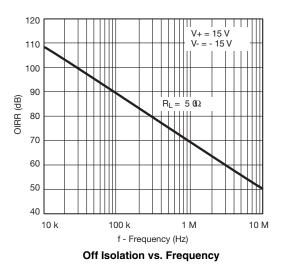
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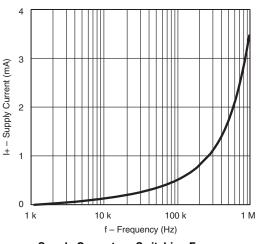
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)





Switching Times vs. Power Supply Voltage





Supply Current vs. Switching Frequency

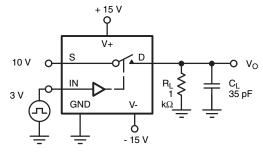
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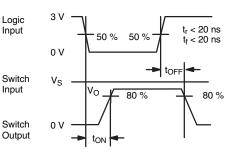


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TEST CIRCUITS



 C_{L} (includes fixture and stray capacitance)



Note:

Logic input waveform is inverted for DG442.

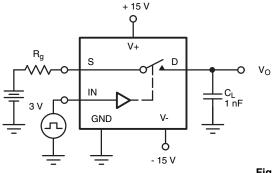
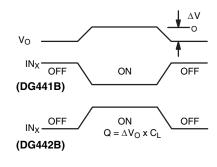
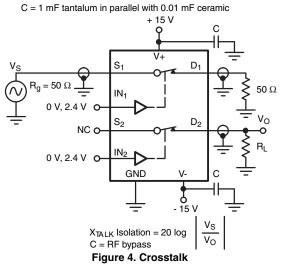
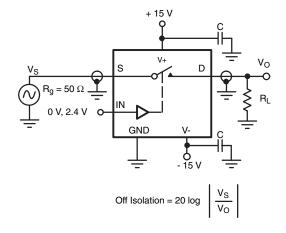


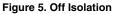


Figure 2. Switching Time









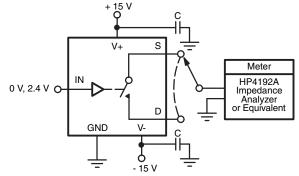


Figure 6. Source/Drain Capacitances

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APPLICATIONS

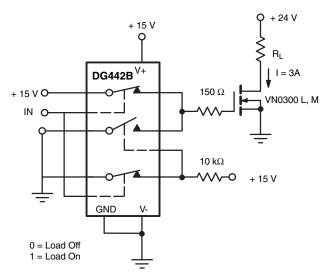


Figure 7. Power MOSFET Driver

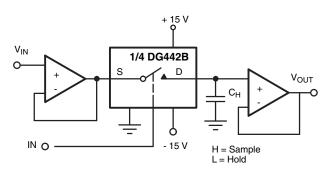


Figure 8. Open Loop Sample-and-Hold

 $R_1 + R_2 + R_3 + R_4$

 R_4

= 100

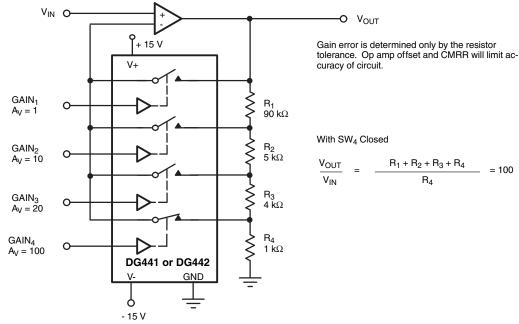


Figure 9. Precision-Weighted Resistor Programmable-Gain Amplifier

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72625.

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SOIC (NARROW): 16-LEAD

JEDEC Part Number: MS-012







PDIP: 16-LEAD





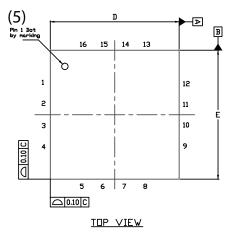


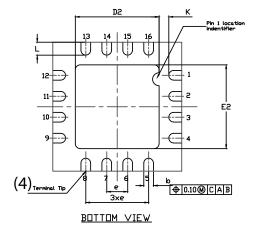
	MILLIN	IETERS	INCHES		
Dim	Min	Max	Min	Max	
Α	3.81	5.08	0.150	0.200	
A ₁	0.38	1.27	0.015	0.050	
В	0.38	0.51	0.015	0.020	
B ₁	0.89	1.65	0.035	0.065	
С	0.20	0.30	0.008	0.012	
D	18.93	21.33	0.745	0.840	
E	7.62	8.26	0.300	0.325	
E ₁	5.59	7.11	0.220	0.280	
e ₁	2.29	2.79	0.090	0.110	
e _A	7.37	7.87	0.290	0.310	
L	2.79	3.81	0.110	0.150	
Q ₁	1.27	2.03	0.050	0.080	
S	0.38	1.52	.015	0.060	
ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482					

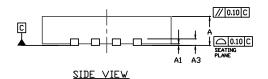
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QFN 4x4-16L Case Outline







VARIATION 1 VARIATION 2 MILLIMETERS(1) MILLIMETERS(1) DIM INCHES INCHES MIN. NOM. MAX. MIN. NOM. MAX. MIN. NOM. MAX. MIN. NOM. MAX. 0.75 0.85 0.95 0.029 0.033 0.037 0.75 0.85 0.95 0.029 0.033 0.037 А 0 -0.05 0 0.002 0 0.05 _ 0.002 A1 -_ 0 A3 0.20 ref. 0.008 ref. 0.20 ref. 0.008 ref. b 0.25 0.30 0.35 0.010 0.012 0.014 0.25 0.30 0.35 0.010 0.012 0.014 4.00 BSC D 0.157 BSC 4.00 BSC 0.157 BSC 0.087 0.106 2.1 2.2 0.083 2.6 2.7 0.102 D2 2.0 0.079 2.5 0.098 0.65 BSC 0.026 BSC 0.65 BSC 0.026 BSC е Е 4.00 BSC 0.157 BSC 4.00 BSC 0.157 BSC 0.087 2.1 2.2 0.083 2.7 0.102 0.106 2.6 E2 2.0 0.079 2.5 0.098 0.20 min. 0.008 min 0.20 min. 0.008 min. Κ 0.5 0.7 0.020 0.024 0.028 0.5 0.016 0.020 L 0.6 0.3 0.4 0.012 N⁽³⁾ 16 16 16 16 Nd⁽³⁾ 4 4 4 4 Ne⁽³⁾ 4 4 4 4

Notes

⁽¹⁾ Use millimeters as the primary measurement.

⁽²⁾ Dimensioning and tolerances conform to ASME Y14.5M. - 1994.

⁽³⁾ N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.

⁽⁴⁾ Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.

⁽⁵⁾ The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.

⁽⁶⁾ Package warpage max. 0.05 mm.

ECN: S13-0893-Rev. B, 22-Apr-13 DWG: 5890

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Document Number: 71921

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Application Note 826

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RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

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